

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

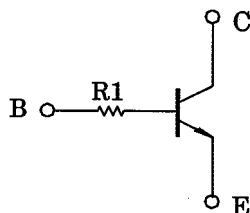
RN1112F, RN1113F

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

Unit: mm

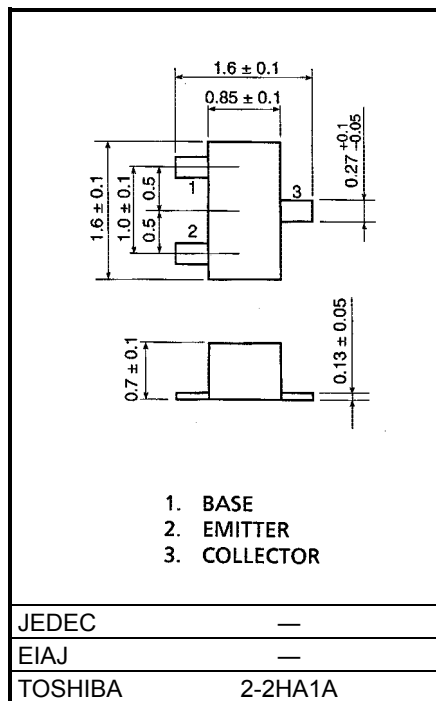
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2112F, RN2113F

Equivalent Circuit



Maximum Ratings (Ta = 25°C)

Characterisitic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C



Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	—	$V_{CB} = 50V, I_E = 0$	—	—	100	nA
Emitter cut-off current	I_{EBO}	—	$V_{EB} = 5V, I_C = 0$	—	—	100	nA
DC current gain	h_{FE}	—	$V_{CE} = 5V, I_C = 1mA$	120	—	700	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	$I_C = 5mA, I_B = 0.25mA$	—	0.1	0.3	V
Translation frequency	f_T	—	$V_{CE} = 10V, I_C = 5mA$	—	250	—	MHz
Collector output capacitance	C_{ob}	—	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	3	6	pF
Input resistor	RN1112F	R1	—	15.4	22	28.6	kΩ
	RN1113F			32.9	47	61.1	

